

### NCE N-Channel Enhancement Mode Power MOSFET

### **Description**

The NCE3400AY uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

#### **General Features**

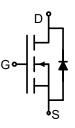
•  $V_{DS} = 30V, I_D = 5.8A$ 

 $R_{DS(ON)}$  < 45m $\Omega$  @  $V_{GS}$ =2.5V

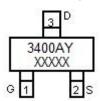
 $R_{DS(ON)}$  < 31m $\Omega$  @  $V_{GS}$ =4.5V

 $R_{DS(ON)}$  < 27m $\Omega$  @  $V_{GS}$ =10V

- High power and current handing capability
- Lead free product is acquired
- Surface mount package
- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



SOT23-3L top view

## **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3400AY	NCE3400AY	SOT23-3L	Ø180mm	8 mm	3000 units

# Absolute Maximum Ratings (T<sub>A</sub>=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	30	V
Gate-Source Voltage	Vgs	±12	V
Drain Current-Continuous	I <sub>D</sub>	5.8	Α
Drain Current-Pulsed (Note 1)	I <sub>DM</sub>	30	Α
Maximum Power Dissipation	P <sub>D</sub>	1.4	W
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 150	$^{\circ}$

#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient (Note 2)	R <sub>0JA</sub>	89	°C/W
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# **Electrical Characteristics (T<sub>A</sub>=25 ℃ unless otherwise noted)**

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	30	33	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V,V <sub>GS</sub> =0V	-	-	1	μA

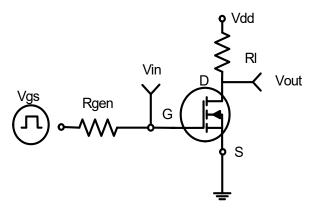
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Gate-Body Leakage Current	lgss	V <sub>GS</sub> =±12V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)	'		'	•		<u> </u>
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS},I_{D}=250\mu A$	0.7	0.9	1.4	V
Drain-Source On-State Resistance		V <sub>GS</sub> =2.5V, I <sub>D</sub> =4A	-	24	45	mΩ
	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A	-	21	31	mΩ
		V <sub>GS</sub> =10V, I <sub>D</sub> =5.8A	-	20	27	mΩ
Forward Transconductance	<b>g</b> FS	$V_{DS}=5V,I_{D}=5A$	10	-	-	S
Dynamic Characteristics (Note4)						•
Input Capacitance	C <sub>lss</sub>	\/ -45\/\/ -0\/	-	825	-	PF
Output Capacitance	Coss	V <sub>DS</sub> =15V,V <sub>GS</sub> =0V, F=1.0MHz	-	100	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	78	-	PF
Switching Characteristics (Note 4)			•			•
Turn-on Delay Time	t <sub>d(on)</sub>		-	3.3	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =15 $V$ , $R_L$ =2.7 $\Omega$	-	4.8	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10V, $R_{GEN}$ =3 $\Omega$	-	26	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	4	-	nS
Total Gate Charge	Qg	V <sub>DS</sub> =15V,I <sub>D</sub> =5.8A,	-	10	-	nC
Gate-Source Charge	Qgs		-	1.6	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	$V_{GS}$ =4.5 $V$	-	3.1	-	nC
Drain-Source Diode Characteristics				•		
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =5.8A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		_	-	5.8	Α

### Notes:

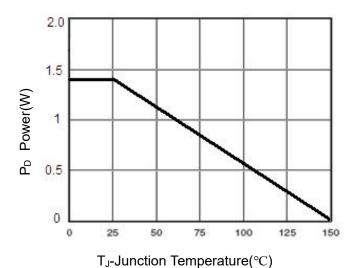
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤  $300\mu$ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



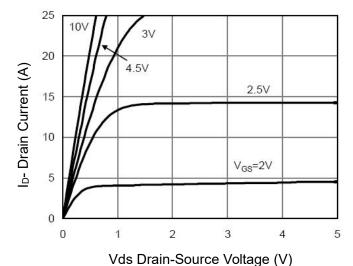
# **Typical Electrical and Thermal Characteristics**



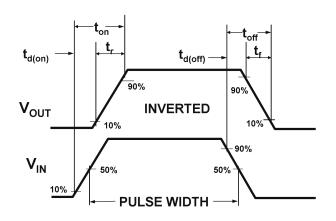
**Figure 1:Switching Test Circuit** 



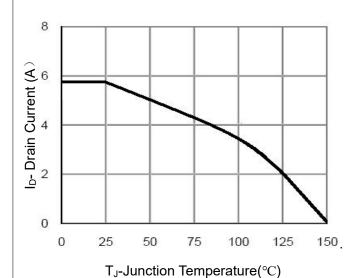
**Figure 3 Power Dissipation** 



**Figure 5 Output Characteristics** 



**Figure 2:Switching Waveforms** 



**Figure 4 Drain Current** 

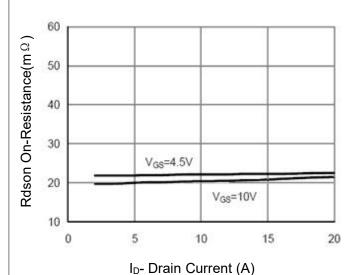
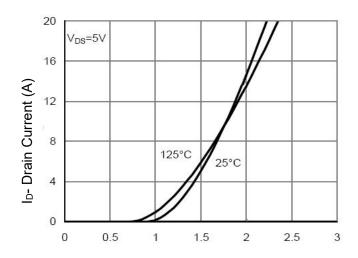
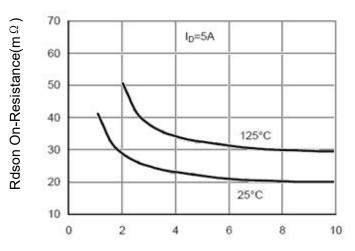


Figure 6 Drain-Source On-Resistance





Vgs Gate-Source Voltage (V)
Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)

Figure 9 Rdson vs Vgs

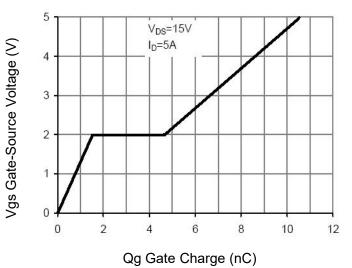
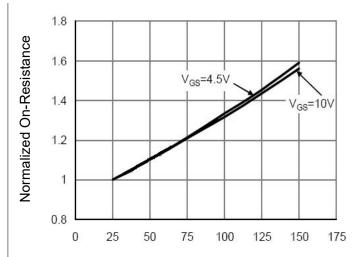


Figure 11 Gate Charge



T<sub>J</sub>-Junction Temperature(°C)

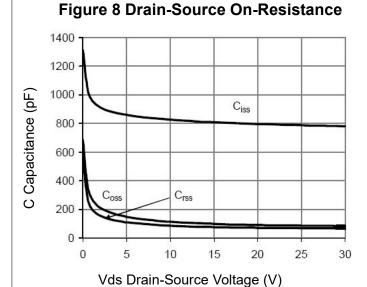


Figure 10 Capacitance vs Vds

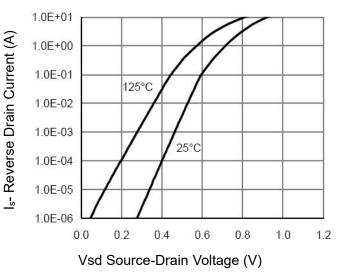
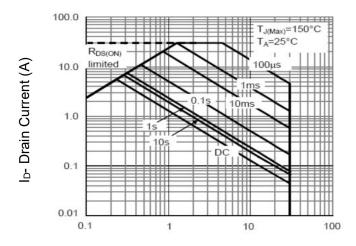


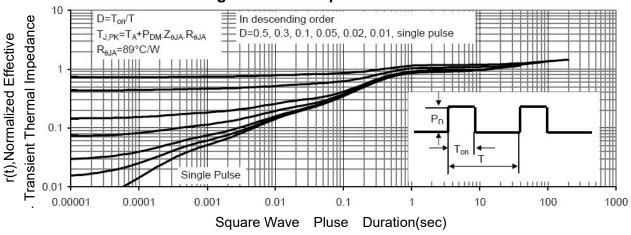
Figure 12 Source- Drain Diode Forward





Vds Drain-Source Voltage (V)

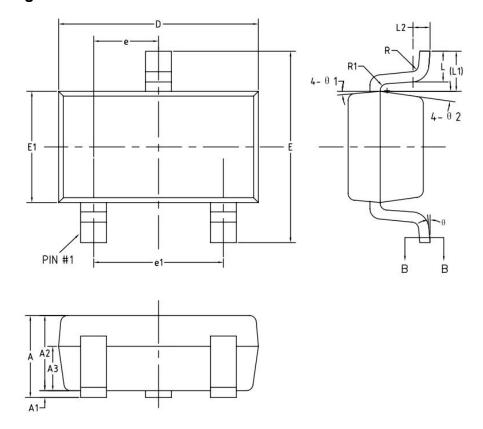
# Figure 13 Safe Operation Area



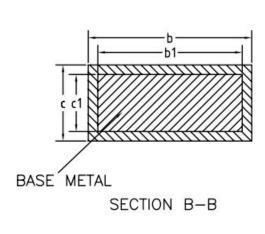
**Figure 14 Normalized Maximum Transient Thermal Impedance** 



# **SOT-23-3L Package Information**



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)



SYMBOL	MIN	NOM	MAX		
Α	1		1.45		
A1	0	8.—8	0.15		
A2	0.90	1.10	1.30		
A3	0.60	0.65	0.70		
b	0.39		0.49		
b1	0.38	0.40	0.45		
С	0.12	12 <del>-</del> 21	0.19		
c1	0.11	0.13	0.15		
D	2.85	2.95	3.05		
E	2.60	2.80	3.00		
E1	1.55	1.65	1.75		
е	0.85	0.95	1.05		
e1	1.80	1.90	2.00		
L	0.35	0.45	0.60		
L1	0.59REF				
L2	0.25BSC				
R	0.05	_			
R1	0.05	<u>-</u>	0.20		
θ	0°	-	8*		
θ 1	8*	10°	12°		
θ 2	8*	10°	12°		



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